

SGL40N150

General Description

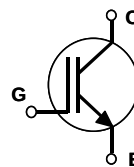
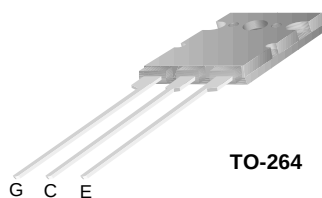
Fairchild's Insulated Gate Bipolar Transistor (IGBT) provides low conduction and switching losses. The SGL40N150 is designed for induction heating applications.

Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)} = 3.7 \text{ V @ } I_C = 40\text{A}$
- High input impedance

Applications

Home appliances, induction heaters, IH JAR, and microwave ovens.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGL40N150	Units
V_{CES}	Collector-Emitter Voltage	1500	V
V_{GES}	Gate-Emitter Voltage	± 25	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	40	A
	Collector Current @ $T_C = 100^\circ\text{C}$	20	A
$I_{CM(1)}$	Pulsed Collector Current	120	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	200	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	80	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	0.625	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	25	$^\circ\text{C/W}$

Electrical Characteristics of the IGBT $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	1500	--	--	V
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 40mA, V_{CE} = V_{GE}$	3.5	5.0	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40A, V_{GE} = 15V$	--	3.7	4.7	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 10V, V_{GE} = 0V,$ $f = 1MHz$	--	4000	--	pF
C_{oes}	Output Capacitance		--	700	--	pF
C_{res}	Reverse Transfer Capacitance		--	300	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600V, I_C = 40A,$ $R_G = 51\Omega, V_{GE} = 15V,$ Resistive Load, $T_C = 25^\circ C$	--	90	200	ns
t_r	Rise Time		--	230	700	ns
$t_{d(off)}$	Turn-Off Delay Time		--	245	400	ns
t_f	Fall Time		--	230	400	ns
Q_g	Total Gate Charge	$V_{CE} = 600V, I_C = 40A,$ $V_{GE} = 15V$	--	140	170	nC
Q_{ge}	Gate-Emitter Charge		--	25	25	nC
Q_{gc}	Gate-Collector Charge		--	45	60	nC

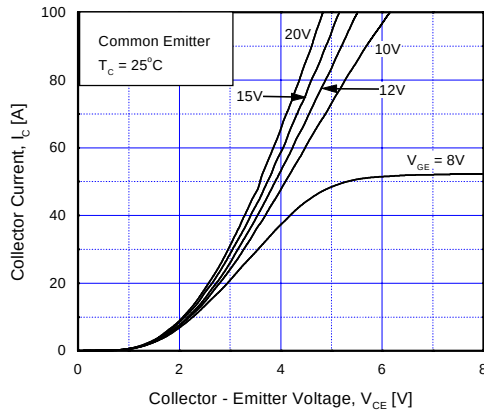


Fig 1. Typical Output Characteristics

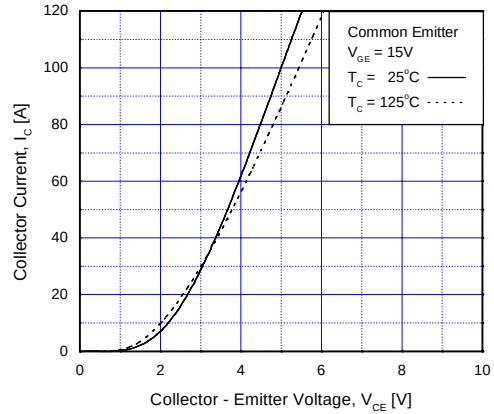


Fig 2. Typical Output Characteristics

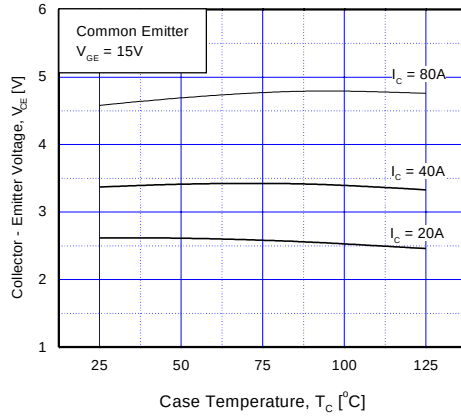


Fig 3. Collector to Emitter Saturation Voltage vs. Case Temperature

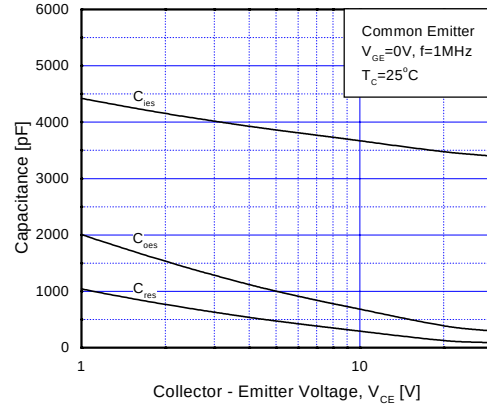


Fig 4. Typical Capacitance vs. Collector to Emitter Voltage

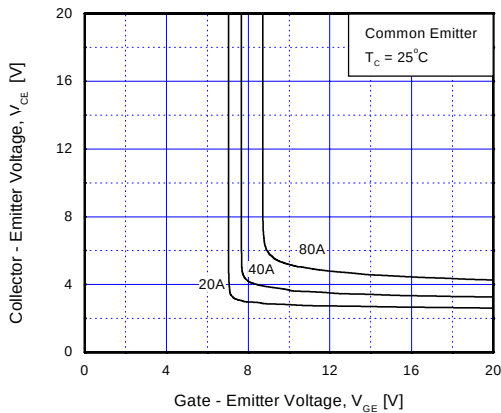


Fig 5. Saturation Voltage vs. V_{GE}

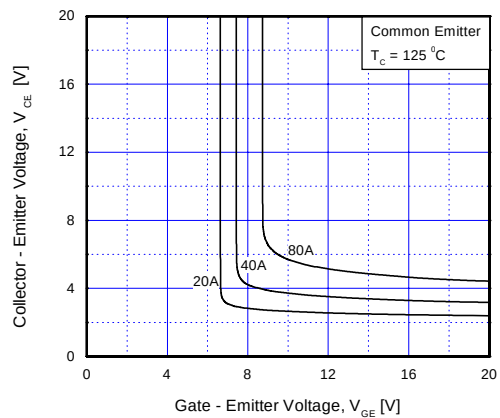


Fig 6. Saturation Voltage vs. V_{GE}

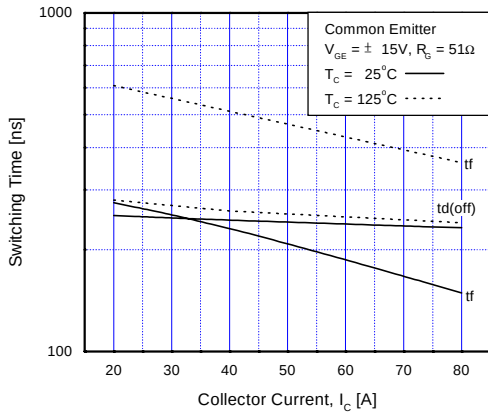


Fig 7. Turn-Off Characteristics vs. Collector Current

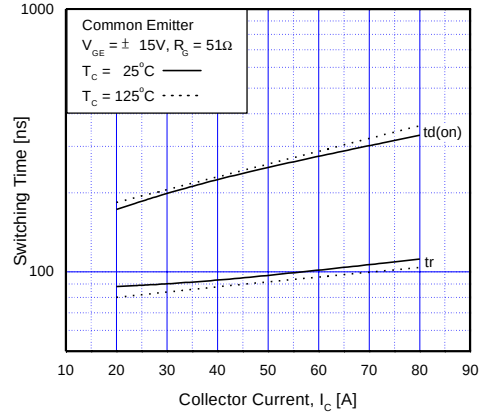


Fig 8. Turn-On Characteristics vs. Collector Current

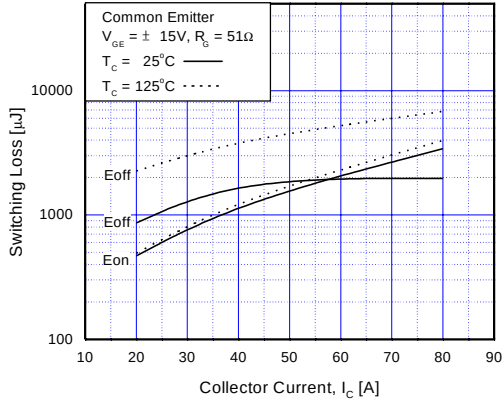


Fig 9. Switching Loss vs. Collector Current

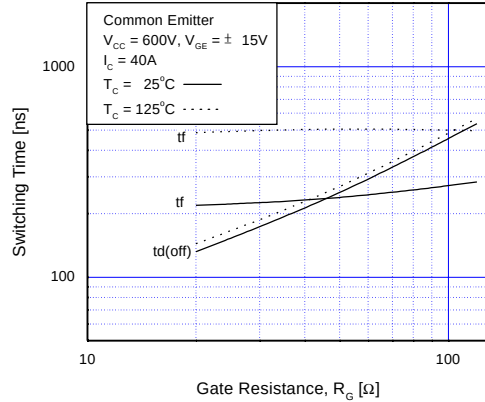


Fig 10. Turn-Off Characteristics vs. Gate Resistance

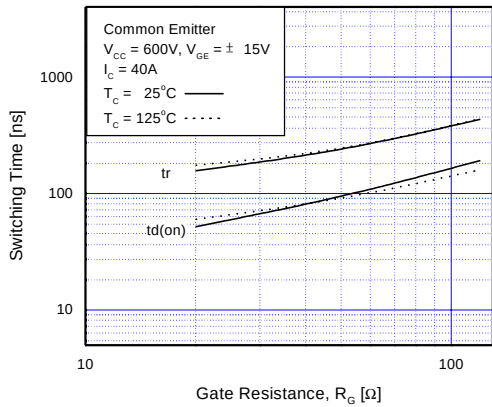


Fig 11. Turn-On Characteristics vs. Gate Resistance

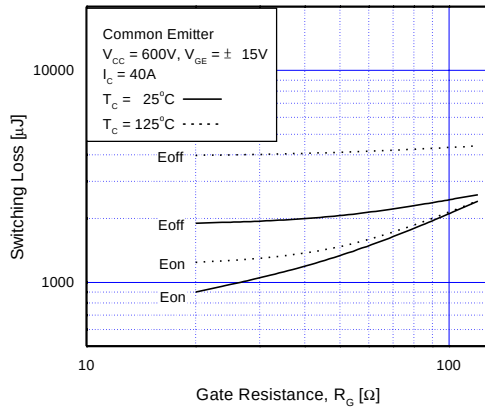


Fig 12. Switching Loss vs. Gate Resistance

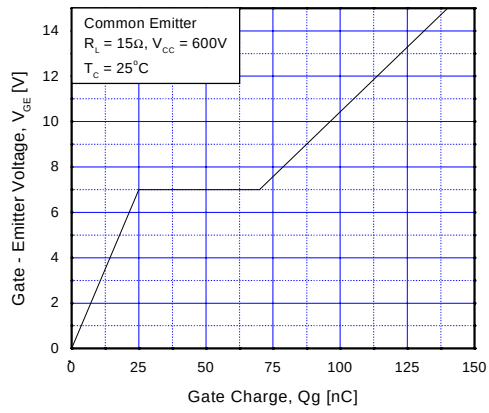


Fig 13. Gate Charge Characteristics

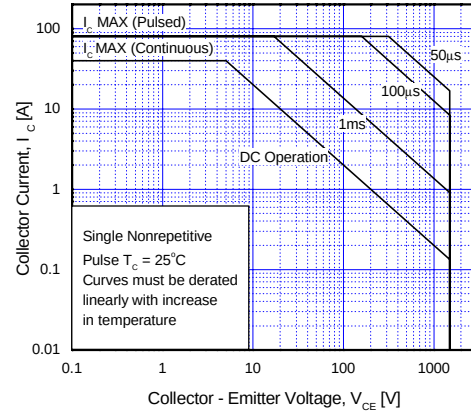


Fig 14. SOA Characteristics

SGL40N150

Technical drawing of a mechanical part, likely a bracket or base plate, showing top and side views with dimensions in millimeters.

Top View Dimensions:

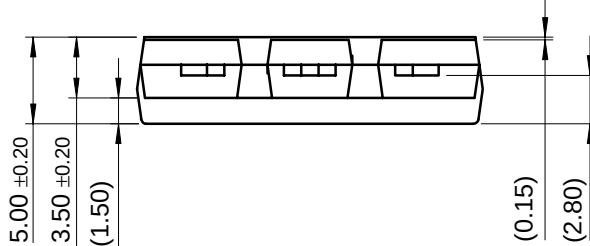
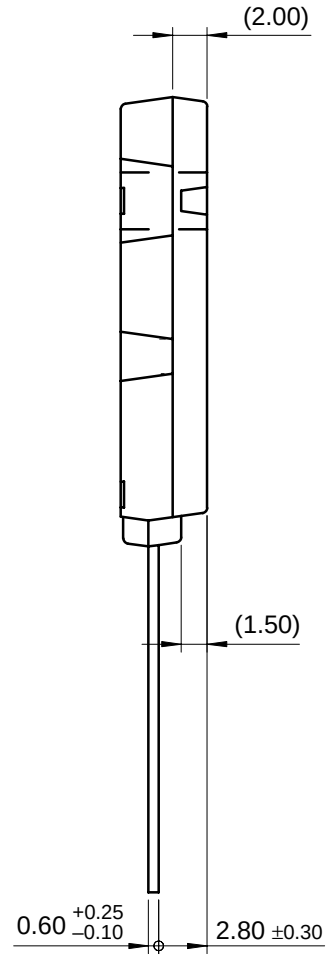
- Overall width: 20.00 ± 0.20
- Overall height: 20.00 ± 0.20
- Central hole diameter: $\phi 3.30 \pm 0.20$
- Corner hole radii: $R1.00$ and $R2.00$
- Distance from center to corner hole center: (8.30)
- Distance from center to corner hole center: (8.30)
- Distance from center to corner hole center: (1.00)
- Distance from center to corner hole center: (4.00)
- Distance from center to corner hole center: (9.00)
- Distance from center to corner hole center: (11.00)
- Distance from center to corner hole center: (7.00)
- Distance from center to corner hole center: (7.00)

Side View Dimensions:

- Overall height: 20.00 ± 0.20
- Base flange thickness: 2.50 ± 0.10
- Distance from base flange to top surface: 1.50 ± 0.20
- Distance from base flange to top surface: (1.50)
- Distance from base flange to top surface: 2.50 ± 0.20
- Distance from base flange to top surface: 3.00 ± 0.20
- Distance from base flange to top surface: $1.00^{+0.25}_{-0.10}$

Material and Tolerances:

- Material: 5.45TYP
- Tolerance: $[5.45 \pm 0.30]$



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SGL40N150 Rev. A1

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